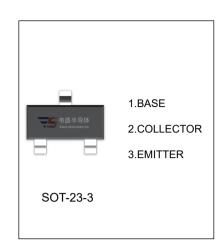


KTC3876 TRANSISTOR (NPN)

FEATURES

- · High hFE
- · Complementary to KTA1505



MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit		
V _{CBO}	Collector-Base Voltage	35	٧		
V _{CEO}	Collector-Emitter Voltage	30	V		
V _{EBO}	Emitter-Base Voltage	mitter-Base Voltage 5			
Ic	Collector Current -Continuous	500	mA		
Pc	Collector Power Dissipation	200	mW		
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55-150	°C		

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions		Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =100 μ A, I _E =0		35			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 1mA, I _B =0		30			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = 100 μ A, I _C =0		5			V
Collector cut-off current	I _{CBO}	V _{CB} = 35V, I _E =0				0.1	μА
Emitter cut-off current	I _{EBO}	V _{EB} = 5V, I _C =0				0.1	μА
	h _{FE1}	V _{CE} =1V, I _C = 100mA		70		400	
DC current gain	h _{FE2}	V _{CE} =6V, I _C = 400mA	0	25			
			Υ	40			
Collector-emitter saturation voltage	V _{CE} (sat)	I _C =100mA, I _B = 10mA				0.25	V
base-emitter voltage	V _{BE}	V _{CE} =1V, I _B = 100mA				1	V
Transition frequency	f _T	V _{CE} =6V, I _C =20mA			300	·	MHz
Collector output capacitance	Cob	V _{CB} =6V,I _E =0,f=1MH _Z			7		pF

CLASSIFICATION OF h_{FE}

Rank	0	Υ	GR(G)
Range	70-140	120-240	200-400
Marking	WO	WY	WG